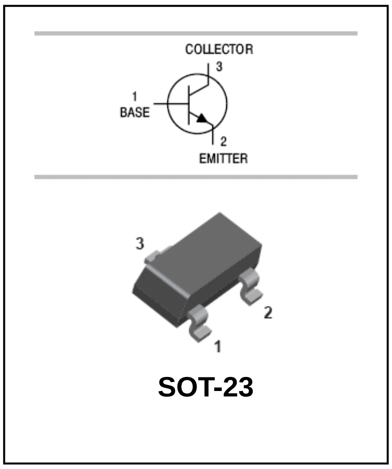
Silicon Epitaxial Planar Transistor **2SC5344**

FEATURES

- High h_{FE}
- Complementary pair with 2SA1981

Lead-free



APPLICATIONS

- General small signal amplifier

ORDERING INFORMATION

Type No.	Marking	Package Code
2SC5344	FAO/FAY	SOT-23

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	**Parameter**	**Value**	**Units**
V_{CBO}	Collector-Base Voltage	35	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	800	mA
P_C	Collector Dissipation	200	mW
$T_{j,}T_{stg}$	Junction and Storage Temperature	-55 to +150	℃

Silicon Epitaxial Planar Transistor **2SC5344**

ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

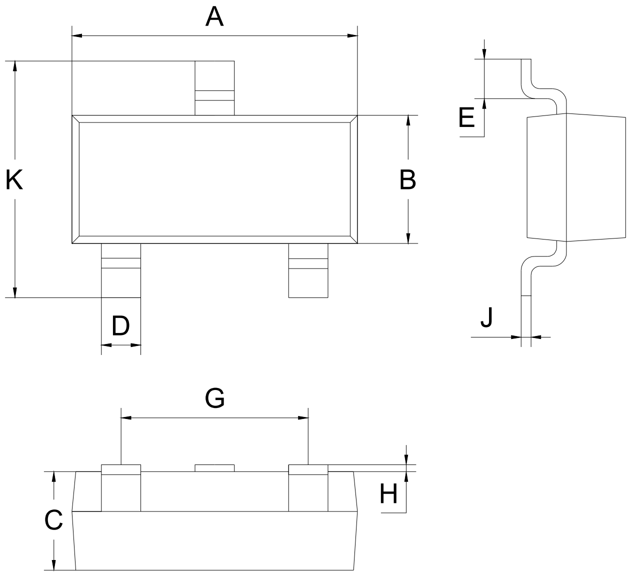
Parameter	**Symbol**	**Test conditions**	**MIN**	**TYP**	**MAX**	**UNIT**
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA,I_E=0	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA,I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=35V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=1V,I_C=100mA	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=500mA, I_B=50mA			0.5	V
Transition frequency	f_T	V_{CE}=5V, I_C= 10mA		120		MHz
Output capacitance	C_{ob}	V_{CB}=10V, I_E=0,f=1MHz		13		pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320
Marking	FAO	FAY

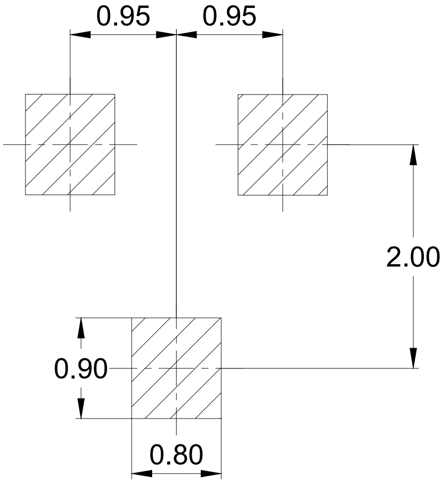
PACKAGE OUTLINE

Plastic surface mounted package SOT-23



SOT-23		
Dim	Min	Max
A	2.70	3.10
B	1.10	1.50
C	1.0 Typical	
D	0.4 Typical	
E	0.35	0.48
G	1.80	2.00
H	0.02	0.1
J	0.1 Typical	
K	2.20	2.60
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
2SC5344	SOT-23	3000/Tape&Reel